

RB521CS-30-HAF

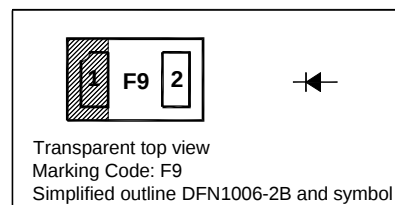
Silicon Epitaxial Planar Schottky Barrier Diode

Features

- Ultra small power mold type
- Low V_F
- High reliability
- Halogen and Antimony Free(HAF), RoHS compliant

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Average Rectified Forward Current	I_O	100	mA
Peak Forward Surge Current (60 Hz for 1 cyc.)	I_{FSM}	0.5	A
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 150	$^\circ\text{C}$

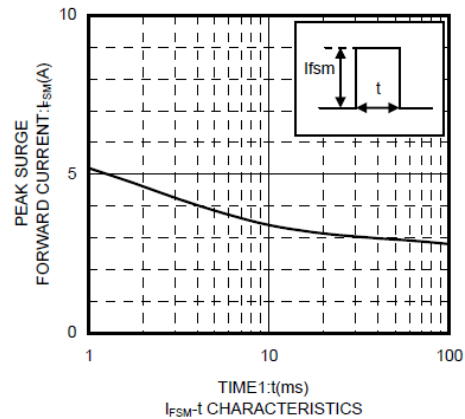
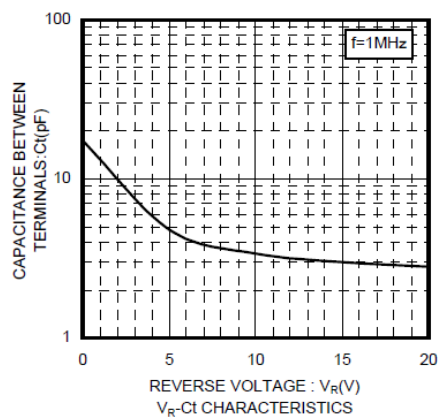
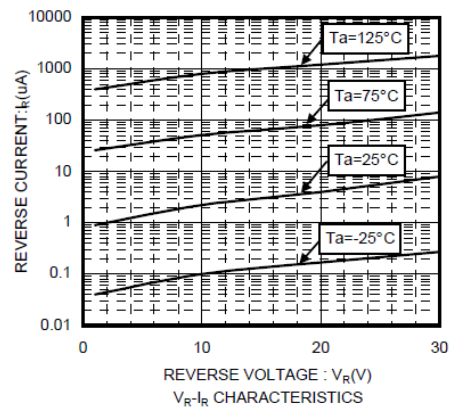
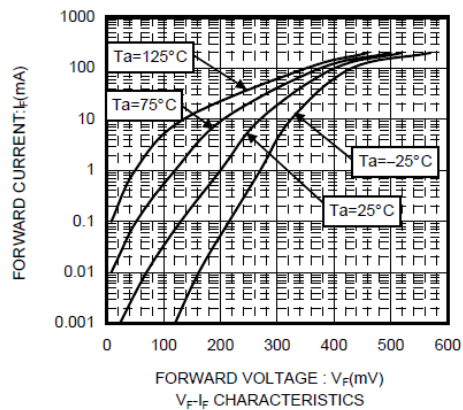
Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	0.35	V
Reverse Current at $V_R = 10\text{ V}$	I_R	7	μA

TOP DYNAMIC



Dated: 10/11/2015 Rev: 03

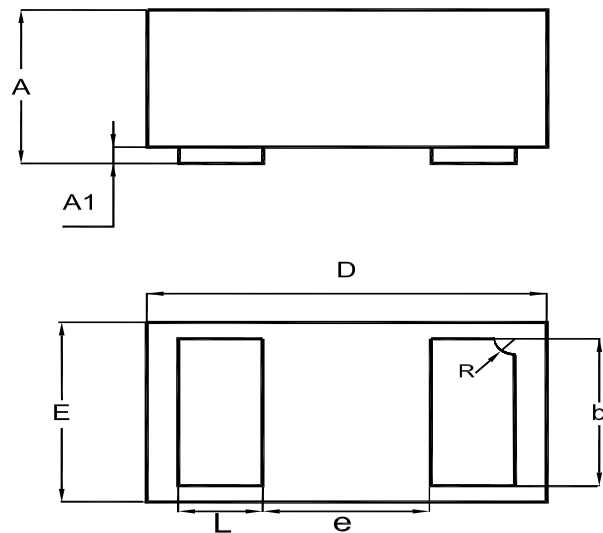


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PACKAGE OUTLINE

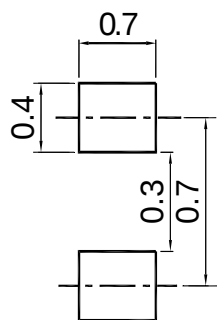
Plastic surface mounted package; 2 leads

DFN1006-2B



UNIT	A	A1	b	D	E	e	L	R
mm	0.40 0.36	0.05 0	0.55 0.45	1.05 0.95	0.65 0.55	0.4	0.3 0.2	0.15 0.05

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
DFN1006-2B	8	4 ± 0.1	0.157 ± 0.004	178	7	5,000

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